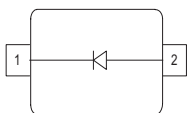


**Silicon Variable Capacitance Diode**

- For UHF-TV-tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure
- Pb-free (RoHS compliant) package



**BB545**  
**BB565/-02V**



Type	Package	Configuration	$L_S$ (nH)	Marking
BB545	SOD323	single	1.8	white U
BB565	SCD80	single	0.6	CC
BB565-02V	SC79	single	0.6	C

**Maximum Ratings** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	30	V
Peak reverse voltage $R \geq 5\text{k}\Omega$	$V_{RM}$	35	
Forward current	$I_F$	20	mA
Operating temperature range	$T_{op}$	-55 ... 150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ... 150	

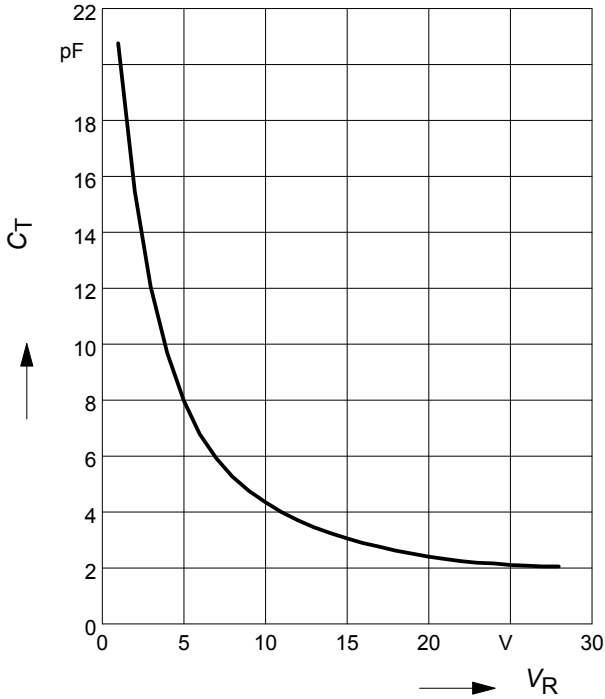
**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Reverse current $V_R = 30\text{ V}$ $V_R = 30\text{ V}, T_A = 85^\circ\text{C}$	$I_R$	- -	- -	10 200	nA
<b>AC Characteristics</b>					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 25\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	$C_T$	18.5 13.2 1.85 1.8	20 14.8 2.07 2	21.5 16.4 2.28 2.2	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	$C_{T1}/C_{T28}$	9	10	11	-
Capacitance ratio $V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$	$C_{T2}/C_{T25}$	6.3	7.2	8.1	-
Capacitance matching <sup>1)</sup> $V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence, BB545}$ $V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 4\text{ diodes sequence, BB565/-02V}$ $V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence, BB565/-02V}$	$\Delta C_T/C_T$	- - -	- 0.5 0.7	2.5 1.5 2	%
Series resistance $V_R = 3\text{ V}, f = 470\text{ MHz}$	$r_S$	-	0.6	-	$\Omega$
Series inductance	$L_S$	-	0.6	-	nH

<sup>1</sup>For details please refer to Application Note 047

**Diode capacitance  $C_T = f(V_R)$**

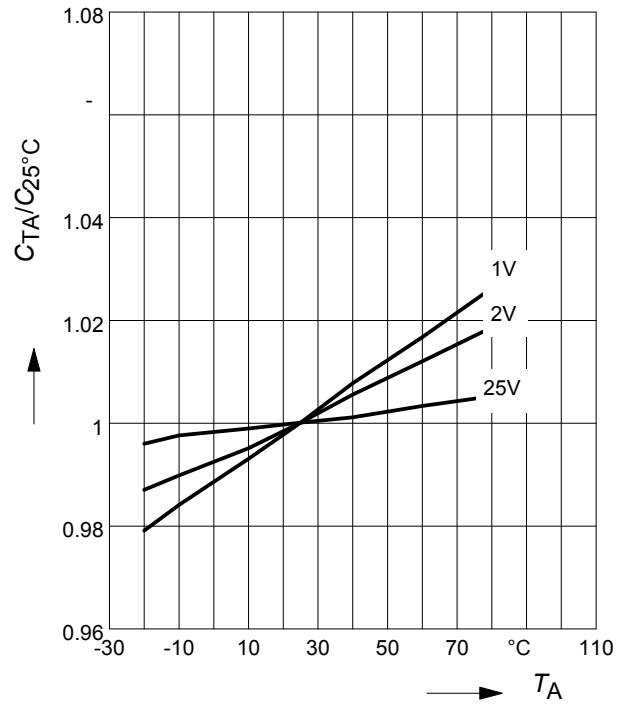
$f = 1\text{MHz}$



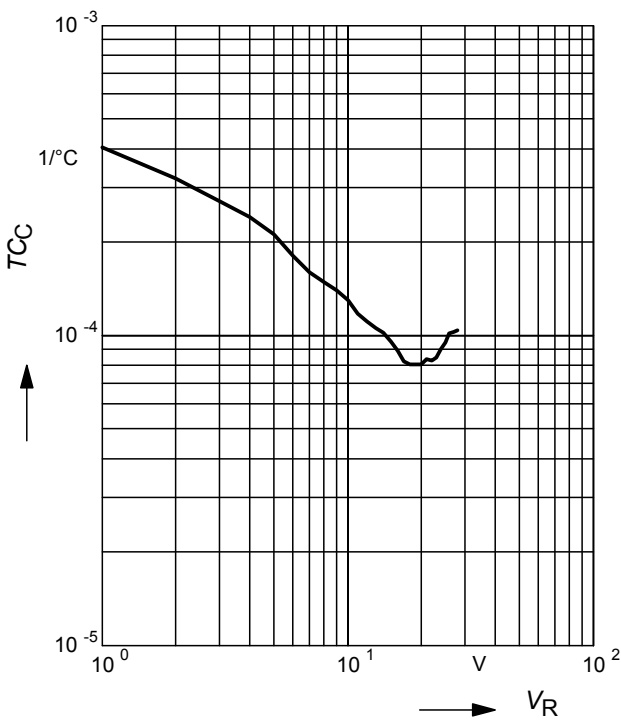
**Normalized diode capacitance**

$C_{(T_A)}/C_{(25^\circ\text{C})} = f(T_A); f = 1\text{MHz}$

$V_R = \text{Parameter}$

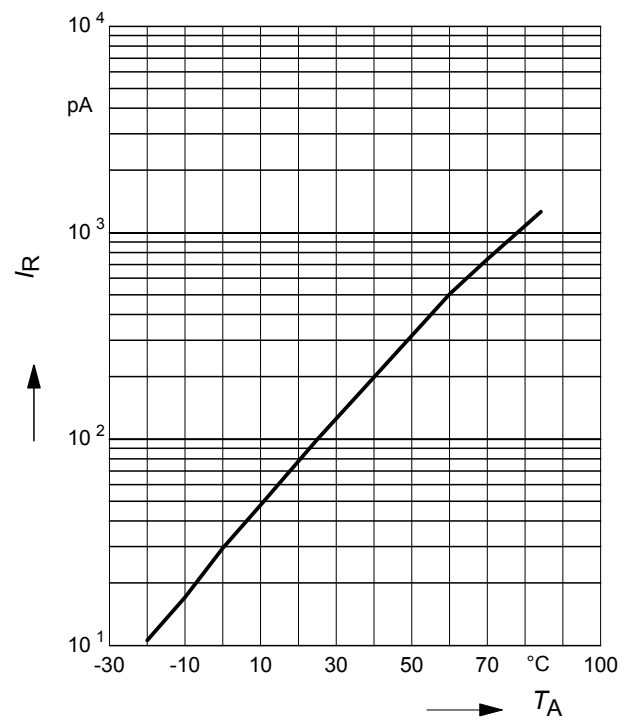


**Temperature coefficient of the diode capacitance  $T_{CC} = f(V_R)$**



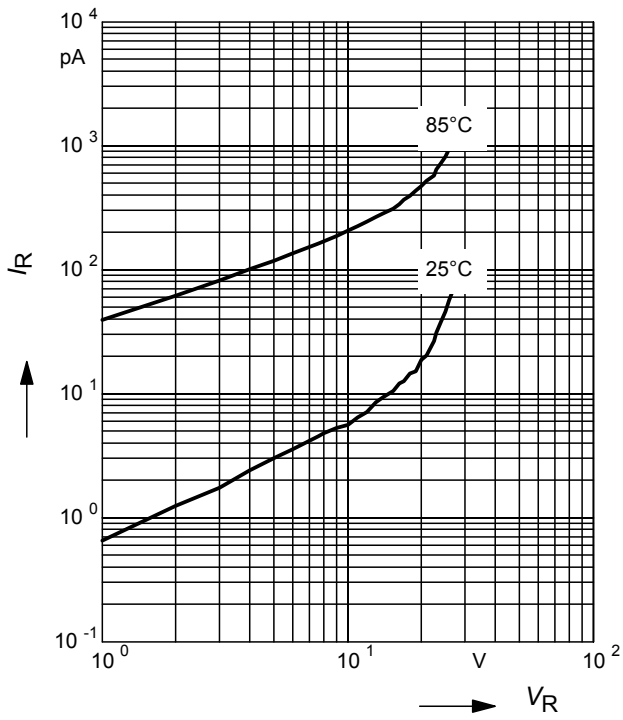
**Reverse current  $I_R = f(T_A)$**

$V_R = 28\text{V}$



Reverse current  $I_R = f(V_R)$

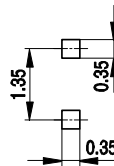
$T_A$  = Parameter



### Package Outline



### Foot Print

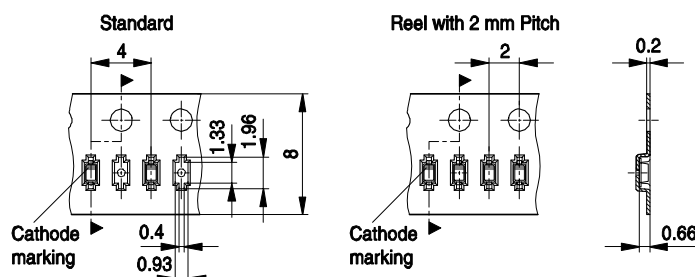


### Marking Layout (Example)

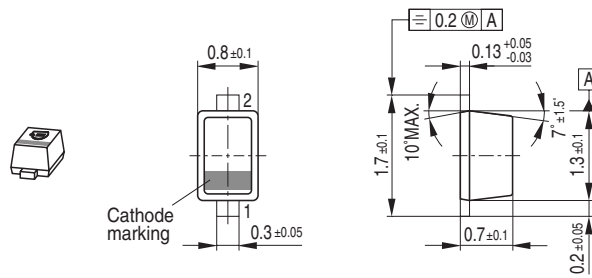


### Standard Packing

- Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel
- Reel  $\varnothing$ 180 mm = 8.000 Pieces/Reel (2 mm Pitch)
- Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



Package Outline



Foot Print



Marking Layout (Example)



Standard Packing

- Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel
- Reel  $\varnothing$ 180 mm = 8.000 Pieces/Reel (2 mm Pitch)
- Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

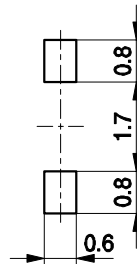
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

Package Outline



Foot Print



Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel





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